

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

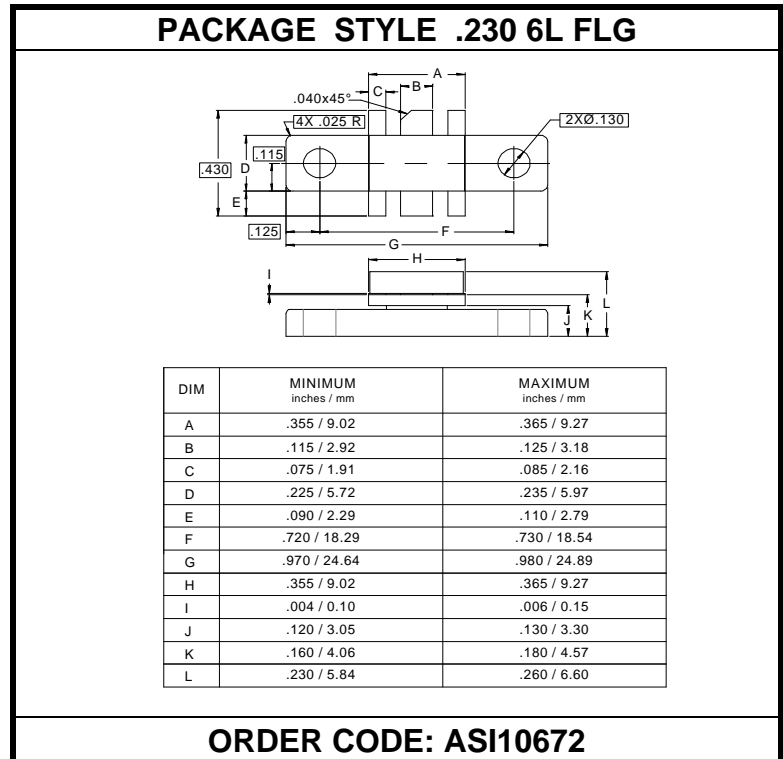
The ASI UHBS60-1 is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	9.0 A
<b>V<sub>CB0</sub></b>	50 V
<b>V<sub>CEO</sub></b>	26 V
<b>V<sub>CES</sub></b>	50 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	190 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	0.9 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 50 mA	50			V
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 50 mA	50			V
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	26			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	3.0			V
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 20 V			10	mA
<b>I<sub>CB0</sub></b>	V <sub>CB</sub> = 30 V			5	mA
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V I <sub>C</sub> = 1.0 A	20		100	---
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 24 V f = 1.0 MHz			75	pF
<b>P<sub>G</sub></b> <b>η<sub>C</sub></b>	V <sub>CE</sub> = 24 V P <sub>OUT</sub> = 60 W f = 900 GHz	7.5	55		dB %